

## Features

- Frequency: 6~8.5GHz
- Gain: 24dB
- Noise Figure: 0.7 dB typ. 0.85dB max.
- Single Power Supply: +4V/55mA
- Output P<sub>-1dB</sub>: 15dBm@8GHz
- Die Size: 1.5mm×1.24mm×0.1mm

## Typical Applications

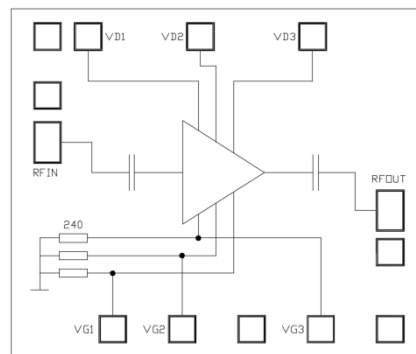
- Radar and ECM
- RF/ Microwave Radio
- Military and Space
- Test and Measurement
- Fiber Optics

## General Description

SAC3075 is a GaAs MMIC low noise amplifier die which operates between 6~8.5GHz. The amplifier can provide 24dB gain, 15dBm Output P<sub>-1dB</sub> and 0.7dB noise figure from a 55mA supply current..

The chip offers full passivation for increased reliability and moisture protection. This amplifier is the perfect alternative to higher cost hybrid amplifiers.

## Functional Diagram



## Electrical Performance ( T<sub>A</sub>=25°C, V<sub>D</sub>=+4V, I<sub>D</sub>=55mA, Z<sub>0</sub>=50Ω )

Parameter	Min.	Typ.	Max.	Units
Frequency Range	6~8.5			GHz
Gain	22	24	27	dB
Gain Flatness	—	±0.75	—	dB
Reverse Isolation	—	-50	—	dB
Input VSWR/ Output VSWR	—	1.5	2	: 1
Noise Figure	—	0.7	0.85	dB
Output P <sub>-1dB</sub>	13	15	—	dBm
Output IP <sub>3</sub>	—	22*	—	dBm
Supply Current(I <sub>D</sub> )	—	40	70	mA
Supply Voltage(V <sub>D</sub> )	3	—	4	V

\*Pout/Tone=0dBm Fc=8GHz, Δf=1MHz

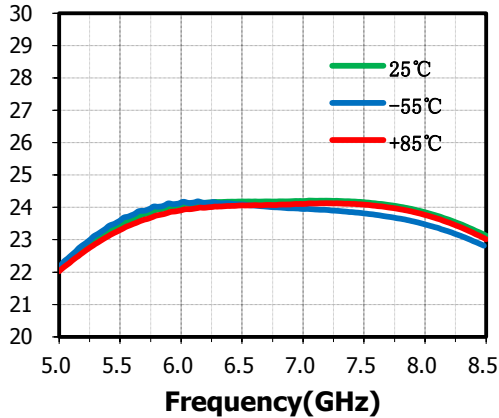
## Absolute Maximum Ratings

Maximum Input Power	+13dBm, CW, 1min	Operating Temperature	-55°C~+85°C
Channel Temperature	+150°C	Storage Temperature	-65°C~+150°C
Supply Voltage	5V		

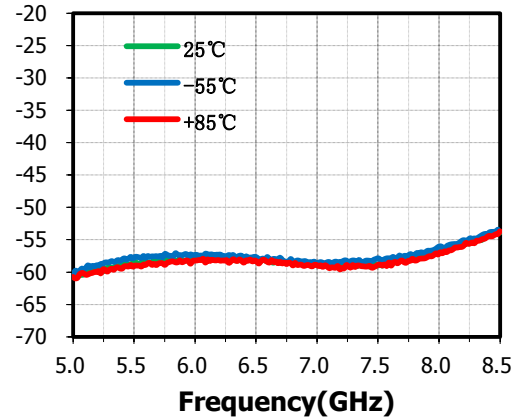
## Typical Performance Curve

VD=+3V, IDQ=45mA

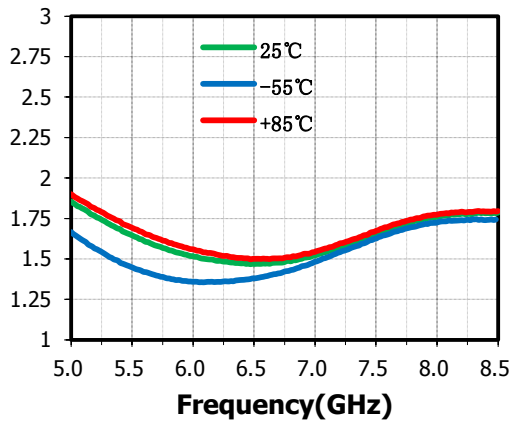
**Small Signal Gain(dB) vs.Temperature**



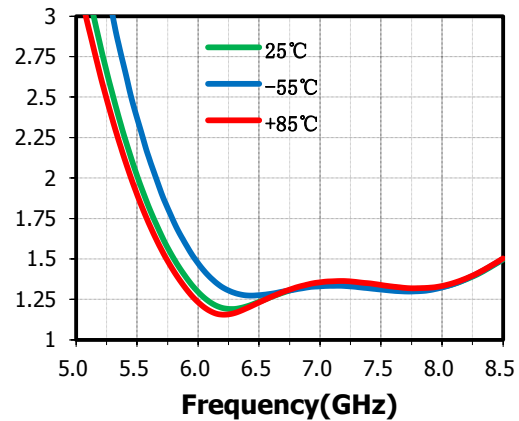
**Reverse Isolation(dB) vs.Temperature**



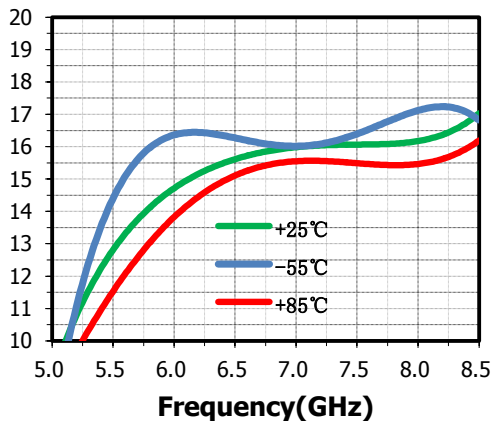
**Input VSWR(:1) vs.Temperature**



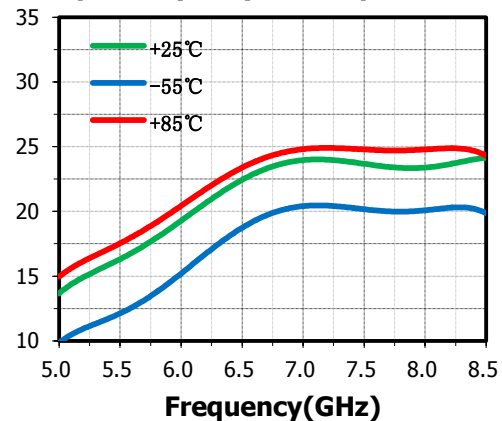
**Output VSWR(:1) vs.Temperature**



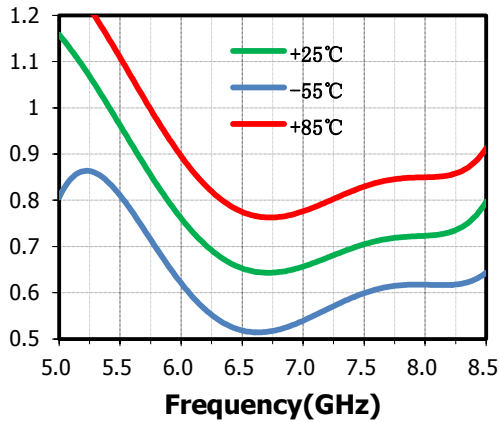
**Output P-1dB(dBm) vs.Temperature**



**Output IP3(dBm) vs.Temperature**

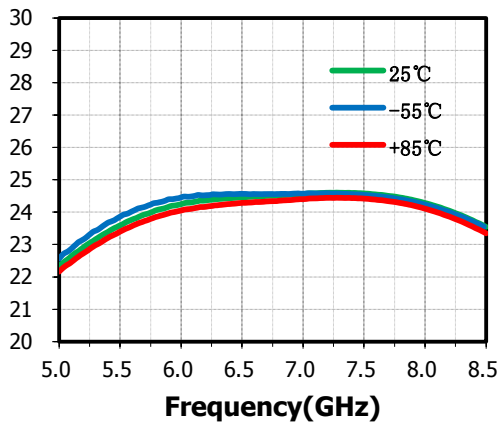


**Noise figure(dB) vs.Temperature**

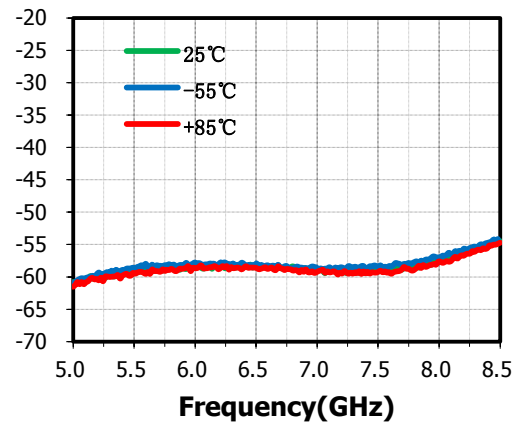


VD=+4V, IDQ=55mA

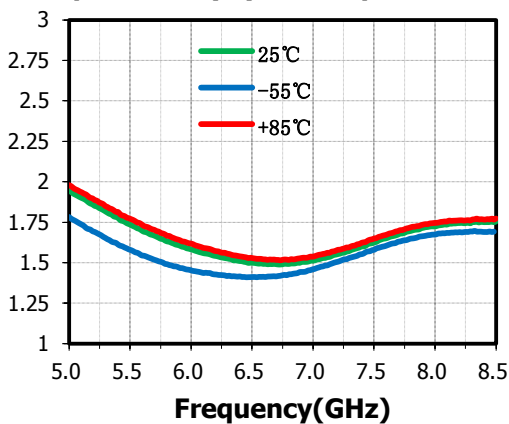
**Small Signal Gain(dB) vs.Temperature**



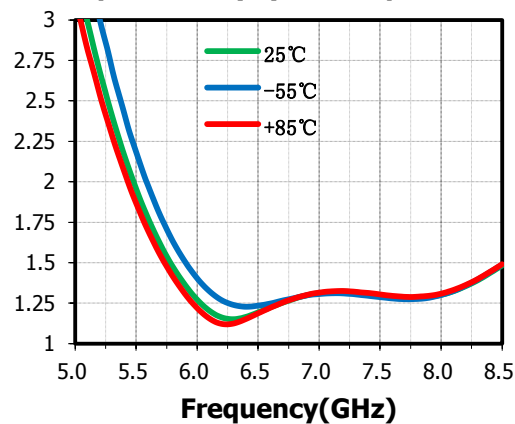
**Reverse Isolation(dB) vs.Temperature**



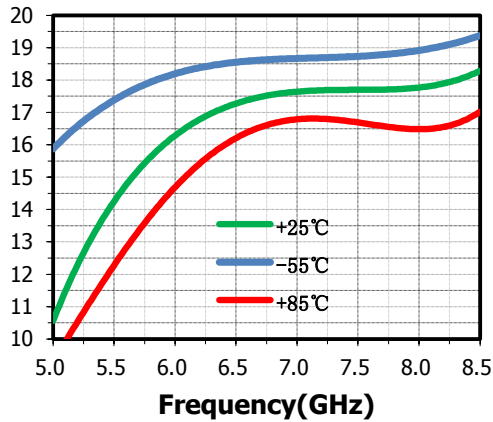
**Input VSWR(:1) vs.Temperature**



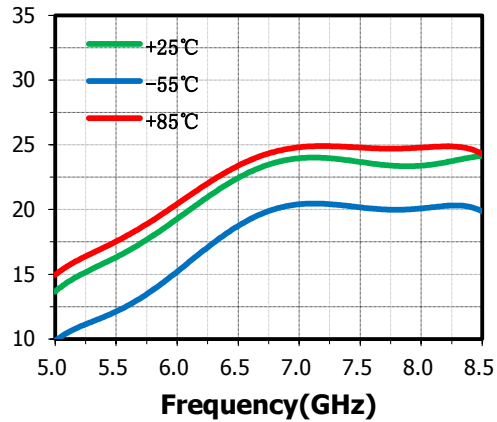
**Output VSWR(:1) vs.Temperature**



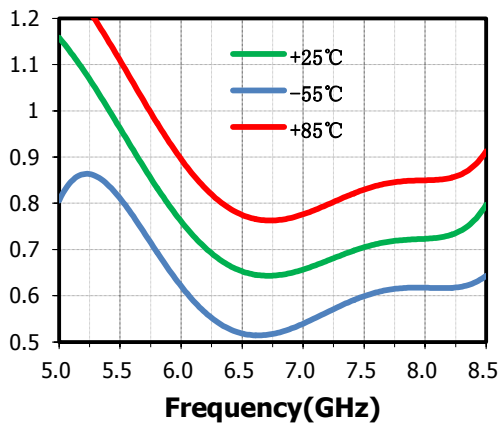
**Output P-1dB(dBm) vs.Temperature**



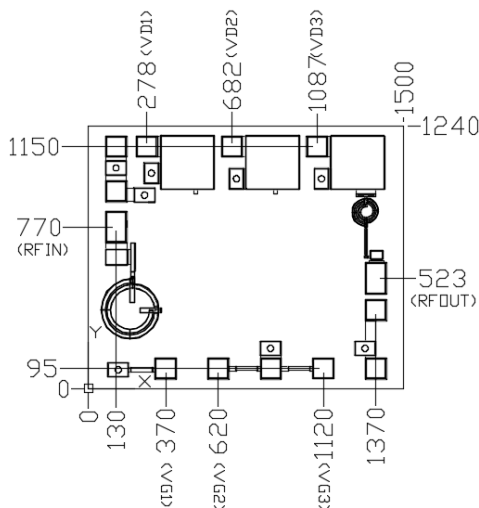
**Output IP<sub>3</sub>(dBm) vs.Temperature**



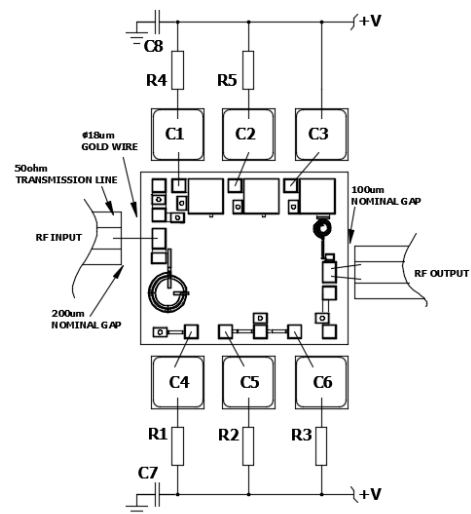
**Noise figure(dB) vs.Temperature**



**Outline  
(All dimensions in μm)**



**Assembly Diagram**



Pads Size: VD1~VD3, VG1~VG3 90\*90μm  
RFIN, RFOUT:90\*130μm

### Components List

Reference Des.	Value	Part Number	Manuf.	Size
R1~R3	1K	—	ANY	0603
C1~C6	100pF	SLC	ANY	—
C7~C8	2.2uF	—	ANY	0603
R4	22R	—	ANY	0603
R5	2.2R	—	ANY	0603

#### Attention:

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.